

EasyPACK™ module with Trench/Fieldstop IGBT H3 and rapid diode and PressFIT / NTC

Features

- Electrical features
 - $V_{CES} = 650 \text{ V}$
 - $I_{C\text{ nom}} = 150 \text{ A} / I_{CRM} = 300 \text{ A}$
 - Increased blocking voltage capability up to 650 V
 - Low inductive design
 - Low switching losses
 - Low $V_{CE,\text{sat}}$
- Mechanical features
 - Al_2O_3 substrate with low thermal resistance
 - Compact design
 - PressFIT contact technology
 - Rugged mounting due to integrated mounting clamps



Potential applications

- Three-level applications
- Motor drives
- Solar applications
- UPS systems

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

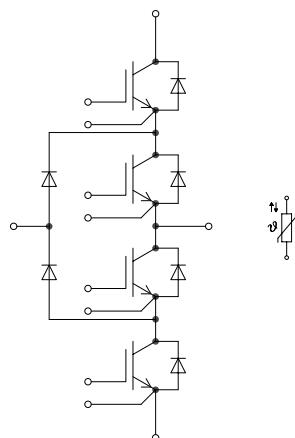


Table of contents

Description	1
Features	1
Potential applications	1
Product validation	1
Table of contents	2
1 Package	3
2 IGBT, T1 / T4	3
3 IGBT, T2 / T3	5
4 Diode, D1 / D4	6
5 Diode, D2 / D3	7
6 Diode, D5 / D6	8
7 NTC-Thermistor	9
8 Characteristics diagrams	10
9 Circuit diagram	18
10 Package outlines	19
11 Module label code	20
Revision history	21
Disclaimer	22

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	3.0	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	11.5	mm
Creepage distance	d_{Creep}	terminal to terminal	6.3	mm
Clearance	d_{Clear}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to terminal	5.0	mm
Comparative tracking index	CTI		>200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{sCE}			15		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_H=25^\circ\text{C}$, per switch		2.8		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting force per clamp	F		40		80	N
Weight	G			39		g

Note: The current under continuous operation is limited to 25A rms per connector pin

2 IGBT, T1 / T4

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		$T_{Vj} = 25^\circ\text{C}$	650	V
Implemented collector current	I_{CN}			150	A
Continuous DC collector current	I_{CDC}	$T_{Vj \max} = 175^\circ\text{C}$	$T_H = 65^\circ\text{C}$	85	A
Repetitive peak collector current	I_{CRM}	$t_p = 1 \text{ ms}$		300	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\text{ sat}}$	$I_C = 150 \text{ A}, V_{GE} = 15 \text{ V}$	$T_{vj} = 25^\circ\text{C}$		1.68	2.00
			$T_{vj} = 125^\circ\text{C}$		1.86	
			$T_{vj} = 150^\circ\text{C}$		1.89	
Gate threshold voltage	$V_{GE\text{th}}$	$I_C = 2.4 \text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^\circ\text{C}$	5.05	5.75	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15 \text{ V}, V_{CE} = 400 \text{ V}$		1.6		μC
Internal gate resistor	$R_{G\text{int}}$	$T_{vj} = 25^\circ\text{C}$		0		Ω
Input capacitance	C_{ies}	$f = 100 \text{ kHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}$		9.4		nF
Reverse transfer capacitance	C_{res}	$f = 100 \text{ kHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}$		0.28		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^\circ\text{C}$		0.009	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}, T_{vj} = 25^\circ\text{C}$			100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 150 \text{ A}, V_{CE} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{G\text{on}} = 7.5 \Omega$	$T_{vj} = 25^\circ\text{C}$		0.057	
			$T_{vj} = 125^\circ\text{C}$		0.059	
			$T_{vj} = 150^\circ\text{C}$		0.059	
Rise time (inductive load)	t_r	$I_C = 150 \text{ A}, V_{CE} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{G\text{on}} = 7.5 \Omega$	$T_{vj} = 25^\circ\text{C}$		0.075	
			$T_{vj} = 125^\circ\text{C}$		0.076	
			$T_{vj} = 150^\circ\text{C}$		0.076	
Turn-off delay time (inductive load)	t_{doff}	$I_C = 150 \text{ A}, V_{CE} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{G\text{off}} = 7.5 \Omega$	$T_{vj} = 25^\circ\text{C}$		0.329	
			$T_{vj} = 125^\circ\text{C}$		0.359	
			$T_{vj} = 150^\circ\text{C}$		0.362	
Fall time (inductive load)	t_f	$I_C = 150 \text{ A}, V_{CE} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{G\text{off}} = 7.5 \Omega$	$T_{vj} = 25^\circ\text{C}$		0.024	
			$T_{vj} = 125^\circ\text{C}$		0.061	
			$T_{vj} = 150^\circ\text{C}$		0.077	
Turn-on energy loss per pulse	E_{on}	$I_C = 150 \text{ A}, V_{CE} = 300 \text{ V}, L_\sigma = 35 \text{ nH}, V_{GE} = \pm 15 \text{ V}, R_{G\text{on}} = 7.5 \Omega, di/dt = 1800 \text{ A}/\mu\text{s}$ ($T_{vj} = 150^\circ\text{C}$)	$T_{vj} = 25^\circ\text{C}$		5.77	
			$T_{vj} = 125^\circ\text{C}$		6.97	
			$T_{vj} = 150^\circ\text{C}$		7.21	
Turn-off energy loss per pulse	E_{off}	$I_C = 150 \text{ A}, V_{CE} = 300 \text{ V}, L_\sigma = 35 \text{ nH}, V_{GE} = \pm 15 \text{ V}, R_{G\text{off}} = 7.5 \Omega, dv/dt = 3600 \text{ V}/\mu\text{s}$ ($T_{vj} = 150^\circ\text{C}$)	$T_{vj} = 25^\circ\text{C}$		2.53	
			$T_{vj} = 125^\circ\text{C}$		3.46	
			$T_{vj} = 150^\circ\text{C}$		3.79	
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT		0.771		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		150	°C

3 IGBT, T2 / T3

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Collector-emitter voltage	V_{CES}	$T_{vj} = 25^\circ\text{C}$	650	V
Implemented collector current	I_{CN}		150	A
Continuous DC collector current	I_{CDC}	$T_{vj \max} = 175^\circ\text{C}$	85	A
Repetitive peak collector current	I_{CRM}	$t_P = 1 \text{ ms}$	300	A
Gate-emitter peak voltage	V_{GES}		± 20	V

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE \text{ sat}}$	$I_C = 150 \text{ A}, V_{GE} = 15 \text{ V}$	$T_{vj} = 25^\circ\text{C}$		1.45	1.90
			$T_{vj} = 125^\circ\text{C}$		1.61	
			$T_{vj} = 150^\circ\text{C}$		1.68	
Gate threshold voltage	$V_{GE \text{ Th}}$	$I_C = 2.4 \text{ mA}, V_{CE} = 20 \text{ V}, T_{vj} = 25^\circ\text{C}$	5.05	5.75	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15 \text{ V}, V_{CE} = 400 \text{ V}$		1.6		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25^\circ\text{C}$		0		Ω
Input capacitance	C_{ies}	$f = 100 \text{ kHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}$		9.2		nF
Reverse transfer capacitance	C_{res}	$f = 100 \text{ kHz}, T_{vj} = 25^\circ\text{C}, V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}$		0.29		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^\circ\text{C}$		0.009	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 650 \text{ V}, V_{GE} = 0 \text{ V}, T_{vj} = 25^\circ\text{C}$			100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 150 \text{ A}, V_{CE} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Gon} = 1.5 \Omega$	$T_{vj} = 25^\circ\text{C}$		0.015	μs
			$T_{vj} = 125^\circ\text{C}$		0.017	
			$T_{vj} = 150^\circ\text{C}$		0.017	
Rise time (inductive load)	t_r	$I_C = 150 \text{ A}, V_{CE} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Gon} = 1.5 \Omega$	$T_{vj} = 25^\circ\text{C}$		0.022	μs
			$T_{vj} = 125^\circ\text{C}$		0.028	
			$T_{vj} = 150^\circ\text{C}$		0.029	
Turn-off delay time (inductive load)	t_{doff}	$I_C = 150 \text{ A}, V_{CE} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 1.5 \Omega$	$T_{vj} = 25^\circ\text{C}$		0.186	μs
			$T_{vj} = 125^\circ\text{C}$		0.211	
			$T_{vj} = 150^\circ\text{C}$		0.216	
Fall time (inductive load)	t_f	$I_C = 150 \text{ A}, V_{CE} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_{Goff} = 1.5 \Omega$	$T_{vj} = 25^\circ\text{C}$		0.094	μs
			$T_{vj} = 125^\circ\text{C}$		0.133	
			$T_{vj} = 150^\circ\text{C}$		0.147	

(table continues...)

Datasheet

Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-on energy loss per pulse	E_{on}	$I_C = 150 \text{ A}$, $V_{CE} = 300 \text{ V}$, $L_\sigma = 35 \text{ nH}$, $V_{GE} = \pm 15 \text{ V}$, $R_{Gon} = 1.5 \Omega$, $di/dt = 4500 \text{ A}/\mu\text{s}$ ($T_{vj} = 150^\circ\text{C}$)	$T_{vj} = 25^\circ\text{C}$		0.341	mJ
			$T_{vj} = 125^\circ\text{C}$		0.629	
			$T_{vj} = 150^\circ\text{C}$		0.719	
Turn-off energy loss per pulse	E_{off}	$I_C = 150 \text{ A}$, $V_{CE} = 300 \text{ V}$, $L_\sigma = 35 \text{ nH}$, $V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 1.5 \Omega$, $dv/dt = 3900 \text{ V}/\mu\text{s}$ ($T_{vj} = 150^\circ\text{C}$)	$T_{vj} = 25^\circ\text{C}$		3.5	mJ
			$T_{vj} = 125^\circ\text{C}$		4.66	
			$T_{vj} = 150^\circ\text{C}$		4.98	
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT		0.771		K/W
Temperature under switching conditions	$T_{vj \text{ op}}$		-40		150	°C

4 Diode, D1 / D4

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition	Values			Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25^\circ\text{C}$	650		V
Continuous DC forward current	I_F			100		A
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$		200		A
I^2t - value	I^2t	$V_R = 0 \text{ V}$, $t_P = 10 \text{ ms}$	$T_{vj} = 125^\circ\text{C}$	1750		A^2s
			$T_{vj} = 150^\circ\text{C}$	1650		

Table 8 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 100 \text{ A}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25^\circ\text{C}$		1.55	V
			$T_{vj} = 125^\circ\text{C}$		1.50	
			$T_{vj} = 150^\circ\text{C}$		1.45	
Peak reverse recovery current	I_{RM}	$I_F = 100 \text{ A}$, $V_R = 300 \text{ V}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 4400 \text{ A}/\mu\text{s}$ ($T_{vj} = 150^\circ\text{C}$)	$T_{vj} = 25^\circ\text{C}$		92.4	A
			$T_{vj} = 125^\circ\text{C}$		102	
			$T_{vj} = 150^\circ\text{C}$		106	

(table continues...)

Table 8 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	Q_r	$I_F = 100 \text{ A}$, $V_R = 300 \text{ V}$, $V_{GE} = -15 \text{ V}$, $-\text{di}_F/\text{dt} = 4400 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		3.93	μC
			$T_{vj} = 125 \text{ }^\circ\text{C}$		7.53	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		8.78	
Reverse recovery energy	E_{rec}	$I_F = 100 \text{ A}$, $V_R = 300 \text{ V}$, $V_{GE} = -15 \text{ V}$, $-\text{di}_F/\text{dt} = 4400 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		0.859	mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.65	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		1.94	
Thermal resistance, junction to heat sink	R_{thJH}	per diode			0.975	K/W
Temperature under switching conditions	$T_{vj op}$		-40		150	$^\circ\text{C}$

5 Diode, D2 / D3

Table 9 Maximum rated values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Repetitive peak reverse voltage	V_{RRM}			650		V
Continuous DC forward current	I_F			100		A
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$		200		A
I^2t - value	I^2t	$V_R = 0 \text{ V}$, $t_P = 10 \text{ ms}$	$T_{vj} = 125 \text{ }^\circ\text{C}$		1750	A^2s
			$T_{vj} = 150 \text{ }^\circ\text{C}$		1650	

Table 10 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 100 \text{ A}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1.55	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.50	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		1.45	
Peak reverse recovery current	I_{RM}	$I_F = 100 \text{ A}$, $V_R = 300 \text{ V}$, $V_{GE} = -15 \text{ V}$, $-\text{di}_F/\text{dt} = 4400 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		92.4	A
			$T_{vj} = 125 \text{ }^\circ\text{C}$		102	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		106	

(table continues...)

Table 10 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	Q_r	$I_F = 100 \text{ A}$, $V_R = 300 \text{ V}$, $V_{GE} = -15 \text{ V}$, $-\text{di}_F/\text{dt} = 4400 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		3.93	μC
			$T_{vj} = 125 \text{ }^\circ\text{C}$		7.53	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		8.78	
Reverse recovery energy	E_{rec}	$I_F = 100 \text{ A}$, $V_R = 300 \text{ V}$, $V_{GE} = -15 \text{ V}$, $-\text{di}_F/\text{dt} = 4400 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		0.859	mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.65	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		1.94	
Thermal resistance, junction to heat sink	R_{thJH}	per diode			0.975	K/W
Temperature under switching conditions	$T_{vj op}$		-40		150	$^\circ\text{C}$

6 Diode, D5 / D6

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Repetitive peak reverse voltage	V_{RRM}			650		V
Continuous DC forward current	I_F			150		A
Repetitive peak forward current	I_{FRM}	$t_P = 1 \text{ ms}$		300		A
I^2t - value	I^2t	$V_R = 0 \text{ V}$, $t_P = 10 \text{ ms}$	$T_{vj} = 125 \text{ }^\circ\text{C}$		2120	A^2s
			$T_{vj} = 150 \text{ }^\circ\text{C}$		1810	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 150 \text{ A}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1.50	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.48	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		1.47	
Peak reverse recovery current	I_{RM}	$I_F = 150 \text{ A}$, $V_R = 300 \text{ V}$, $V_{GE} = -15 \text{ V}$, $-\text{di}_F/\text{dt} = 1800 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		41.8	A
			$T_{vj} = 125 \text{ }^\circ\text{C}$		69.7	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		75.4	

(table continues...)

Table 12 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	Q_r	$I_F = 150 \text{ A}$, $V_R = 300 \text{ V}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 1800 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		4.93	μC
			$T_{vj} = 125 \text{ }^\circ\text{C}$		8.81	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		9.27	
Reverse recovery energy	E_{rec}	$I_F = 150 \text{ A}$, $V_R = 300 \text{ V}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 1800 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		0.426	mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1.02	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		1.22	
Thermal resistance, junction to heat sink	R_{thJH}	per diode			0.888	K/W
Temperature under switching conditions	$T_{vj op}$		-40		150	$^\circ\text{C}$

7 NTC-Thermistor

Table 13 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25 \text{ }^\circ\text{C}$		5		$\text{k}\Omega$
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100 \text{ }^\circ\text{C}$, $R_{100} = 493 \Omega$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25 \text{ }^\circ\text{C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15 \text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15 \text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15 \text{ K}))]$		3433		K

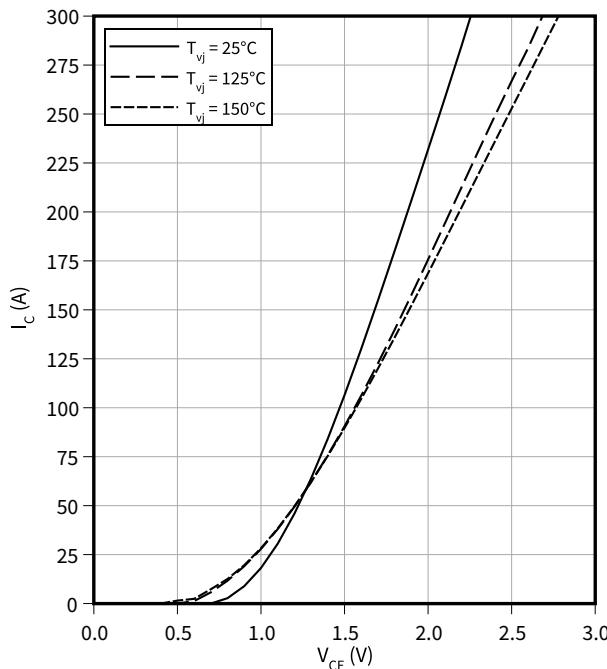
Note: Specification according to the valid application note.

8 Characteristics diagrams

Output characteristic (typical), IGBT, T1 / T4

$$I_C = f(V_{CE})$$

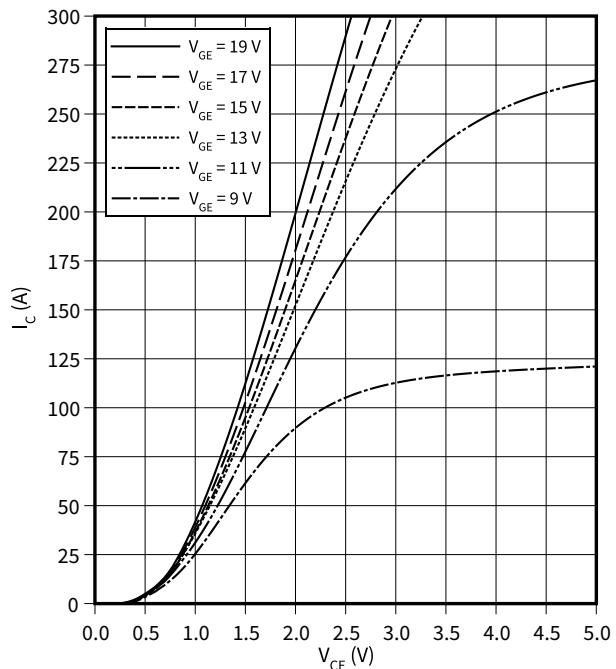
$$V_{GE} = 15 \text{ V}$$



Output characteristic field (typical), IGBT, T1 / T4

$$I_C = f(V_{CE})$$

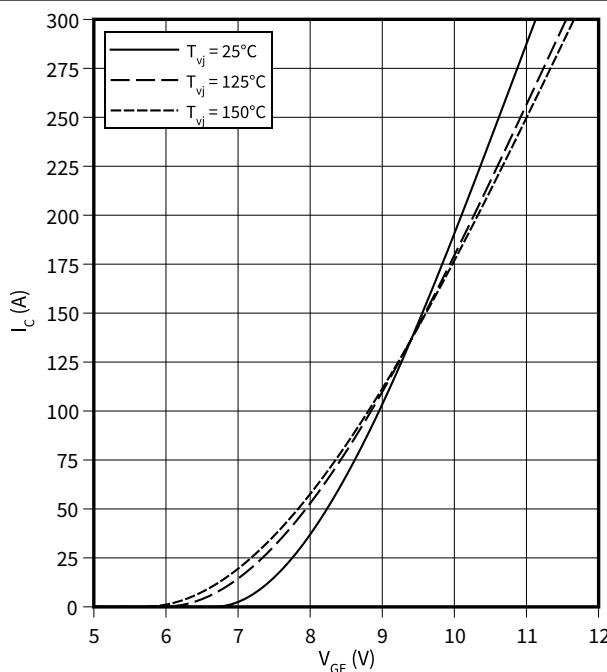
$$T_{vj} = 150 \text{ }^{\circ}\text{C}$$



Transfer characteristic (typical), IGBT, T1 / T4

$$I_C = f(V_{GE})$$

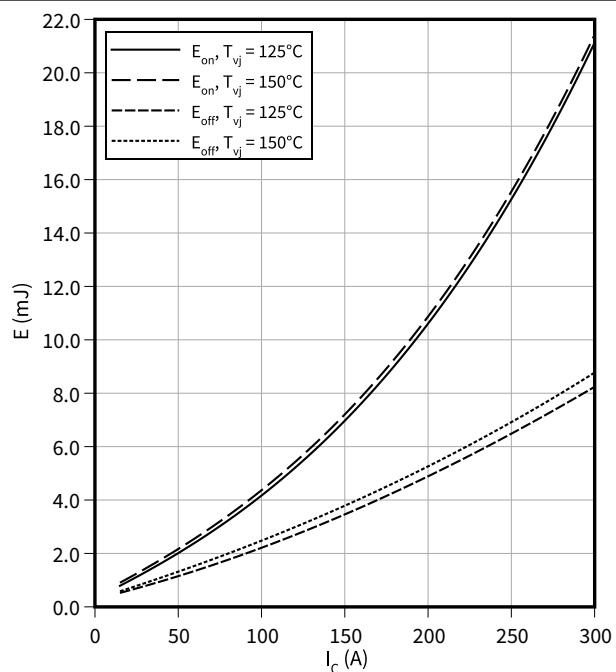
$$V_{CE} = 20 \text{ V}$$



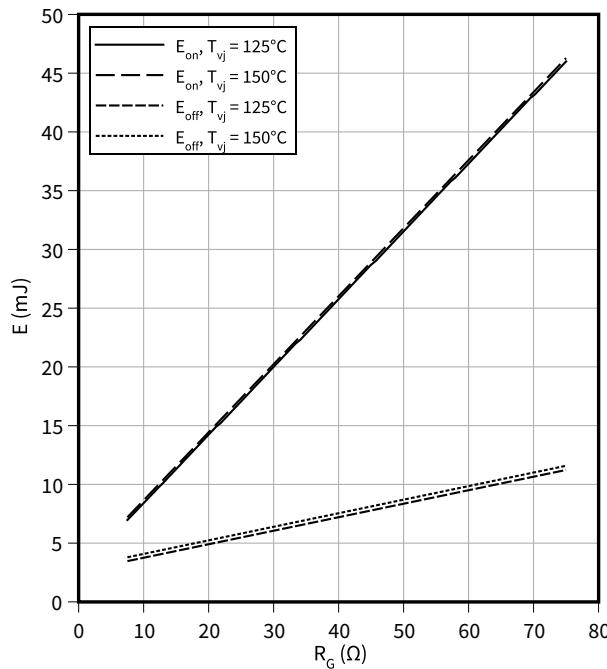
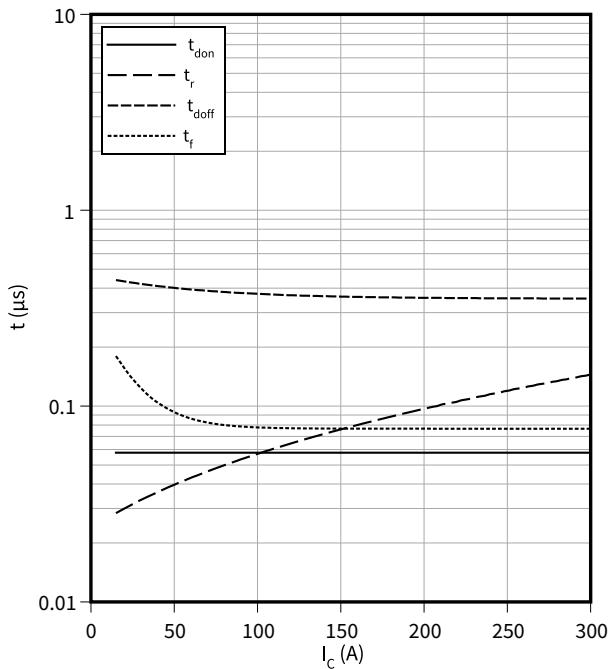
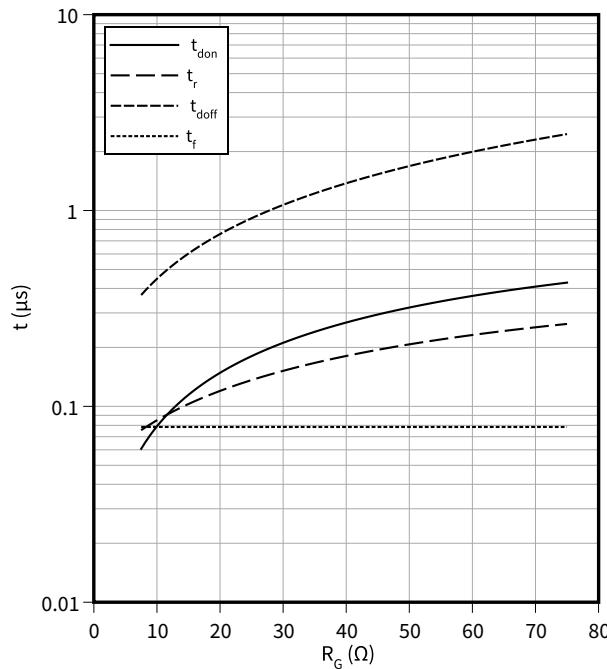
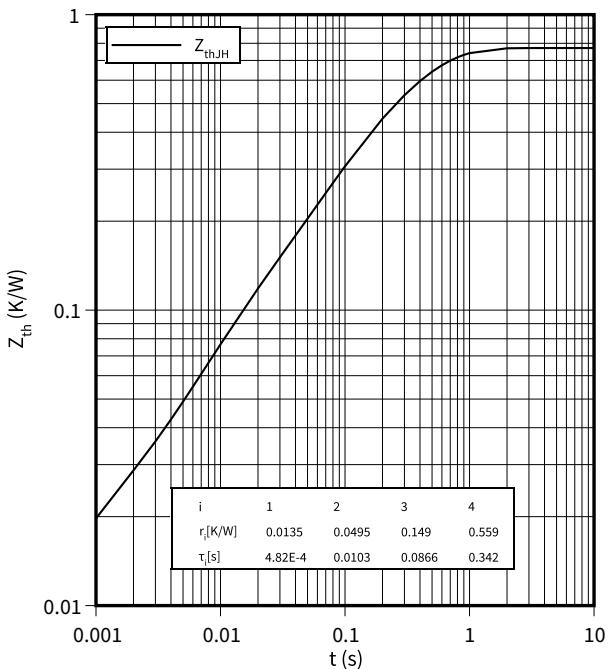
Switching losses (typical), IGBT, T1 / T4

$$E = f(I_C)$$

$$R_{Goff} = 7.5 \Omega, R_{Gon} = 7.5 \Omega, V_{CE} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}$$



8 Characteristics diagrams

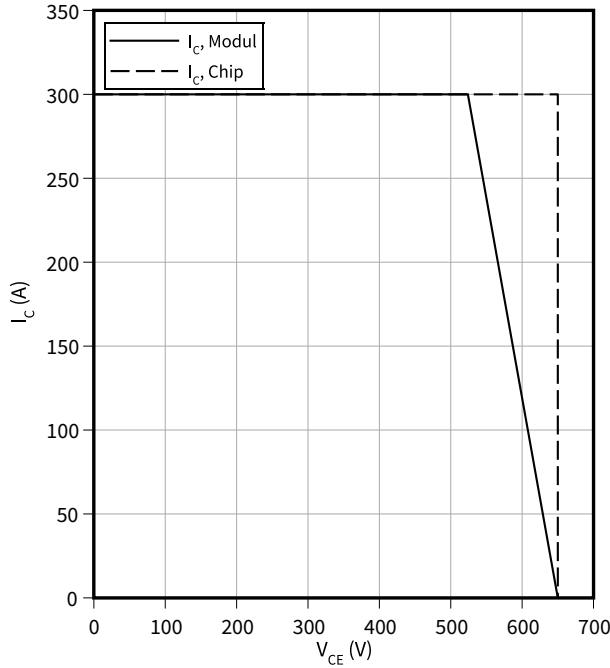
Switching losses (typical), IGBT, T1 / T4 $E = f(R_G)$ $I_C = 150 \text{ A}, V_{CE} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}$ **Switching times (typical), IGBT, T1 / T4** $t = f(I_C)$ $R_{Goff} = 7.5 \Omega, R_{Gon} = 7.5 \Omega, V_{CE} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 150^\circ\text{C}$ **Switching times (typical), IGBT, T1 / T4** $t = f(R_G)$ $I_C = 150 \text{ A}, V_{CE} = 300 \text{ V}, V_{GE} = \pm 15 \text{ V}, T_{vj} = 150^\circ\text{C}$ **Transient thermal impedance , IGBT, T1 / T4** $Z_{th} = f(t)$ 

8 Characteristics diagrams

Reverse bias safe operating area (RBSOA), IGBT, T1 / T4

$$I_C = f(V_{CE})$$

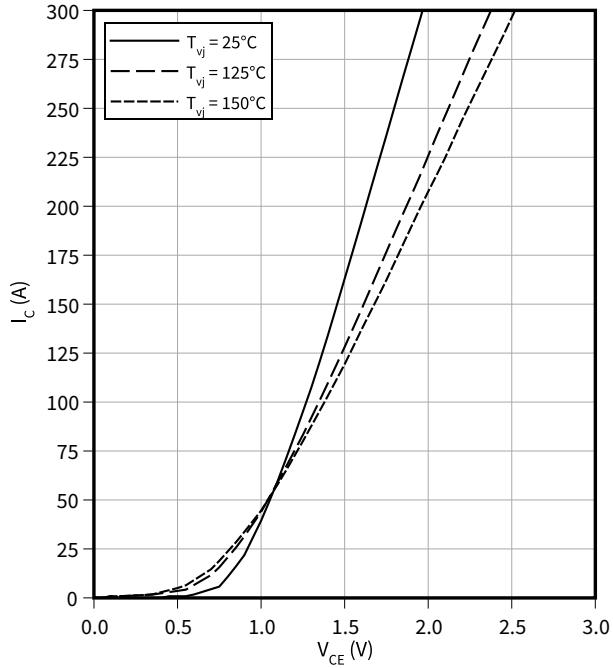
$$R_{Goff} = 7.5 \Omega, V_{GE} = \pm 15 \text{ V}, T_{vj} = 150^\circ\text{C}$$



Output characteristic (typical), IGBT, T2 / T3

$$I_C = f(V_{CE})$$

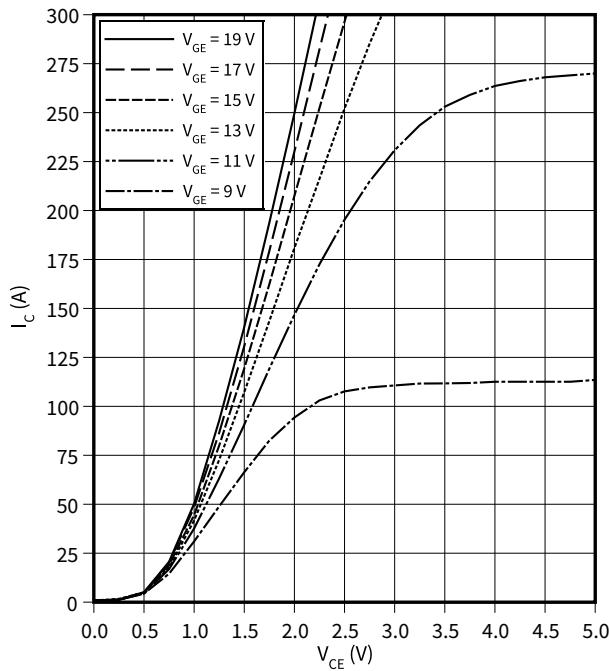
$$V_{GE} = 15 \text{ V}$$



Output characteristic field (typical), IGBT, T2 / T3

$$I_C = f(V_{CE})$$

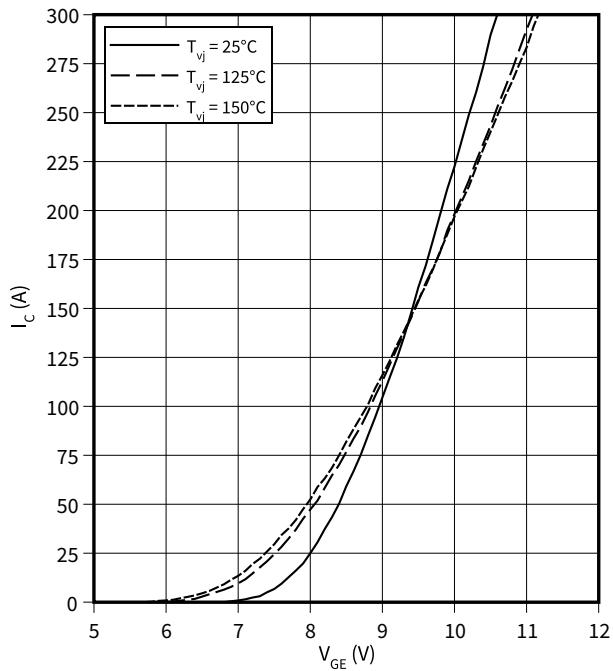
$$T_{vj} = 150^\circ\text{C}$$



Transfer characteristic (typical), IGBT, T2 / T3

$$I_C = f(V_{GE})$$

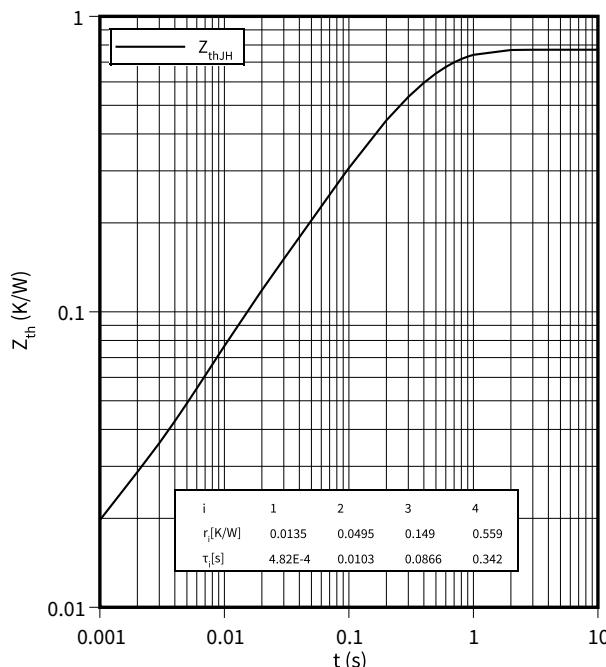
$$V_{CE} = 20 \text{ V}$$



8 Characteristics diagrams

Transient thermal impedance , IGBT, T2 / T3

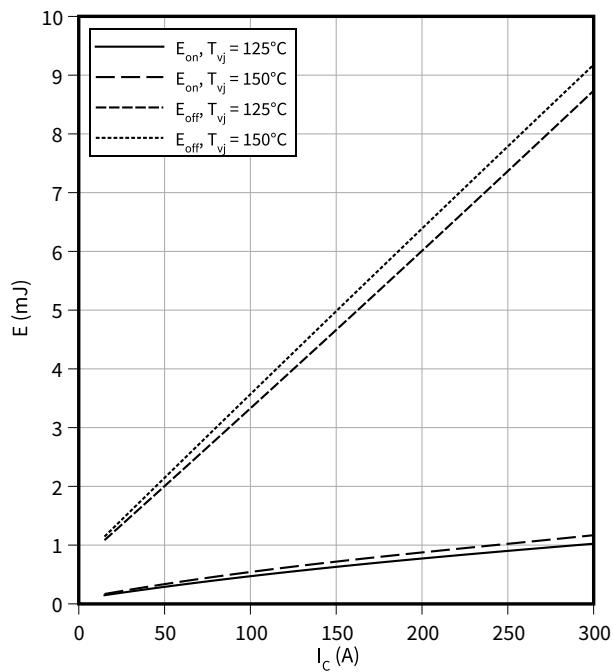
$$Z_{th} = f(t)$$



Switching losses (typical), IGBT, T2 / T3

$$E = f(I_C)$$

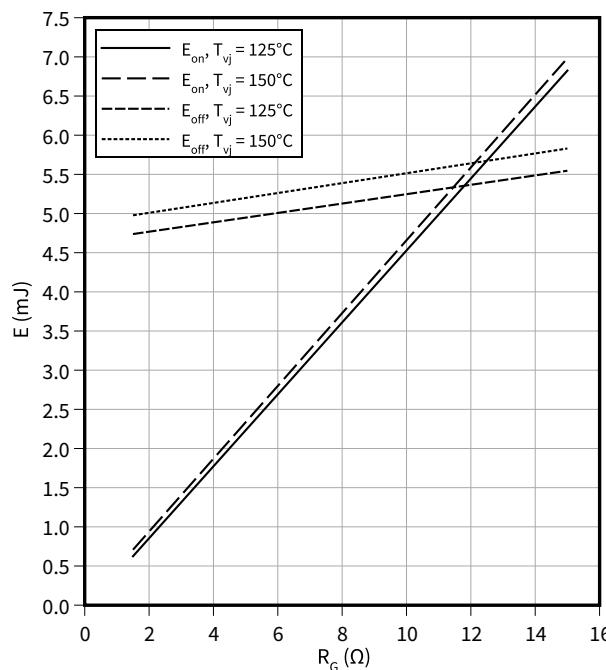
$R_{Goff} = 1.5 \Omega$, $R_{Gon} = 1.5 \Omega$, $V_{GE} = \pm 15 V$, $V_{CE} = 300 V$



Switching losses (typical), IGBT, T2 / T3

$$E = f(R_G)$$

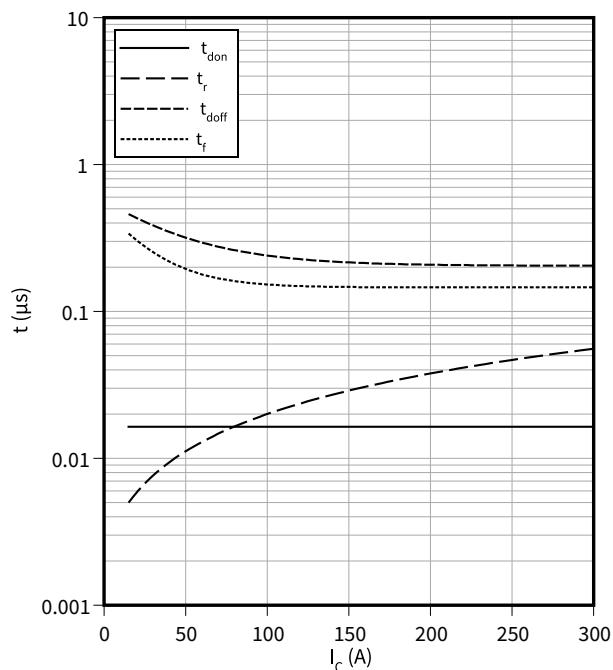
$V_{GE} = \pm 15 V$, $I_C = 150 A$, $V_{CE} = 300 V$



Switching times (typical), IGBT, T2 / T3

$$t = f(I_C)$$

$R_{Goff} = 1.5 \Omega$, $R_{Gon} = 1.5 \Omega$, $V_{GE} = \pm 15 V$, $V_{CE} = 300 V$, $T_{vj} = 150^\circ C$

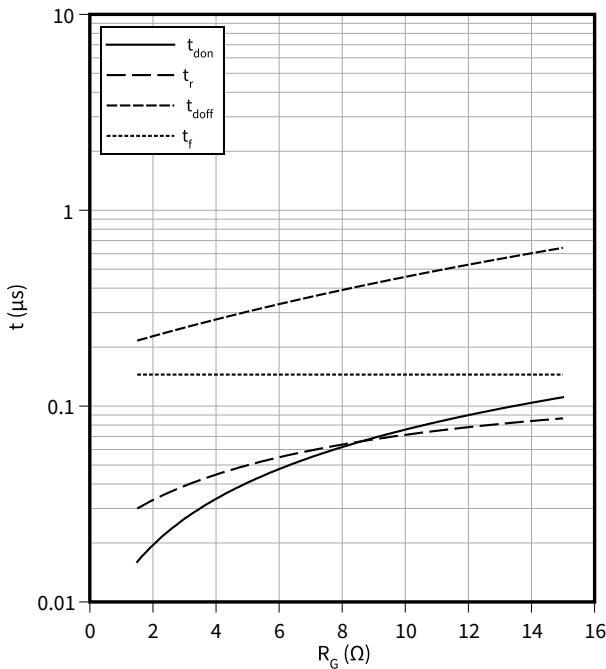


8 Characteristics diagrams

Switching times (typical), IGBT, T2 / T3

$t = f(R_G)$

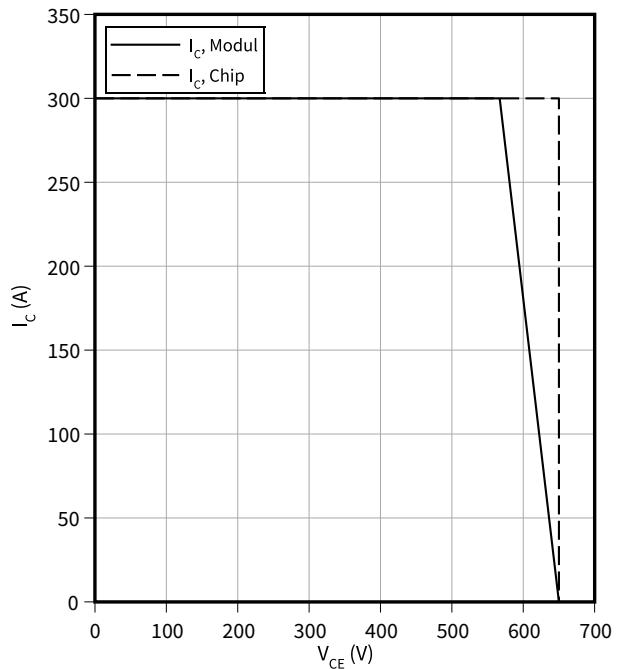
$V_{GE} = \pm 15 \text{ V}$, $I_C = 150 \text{ A}$, $V_{CE} = 300 \text{ V}$, $T_{vj} = 150^\circ\text{C}$



Reverse bias safe operating area (RBSOA), IGBT, T2 / T3

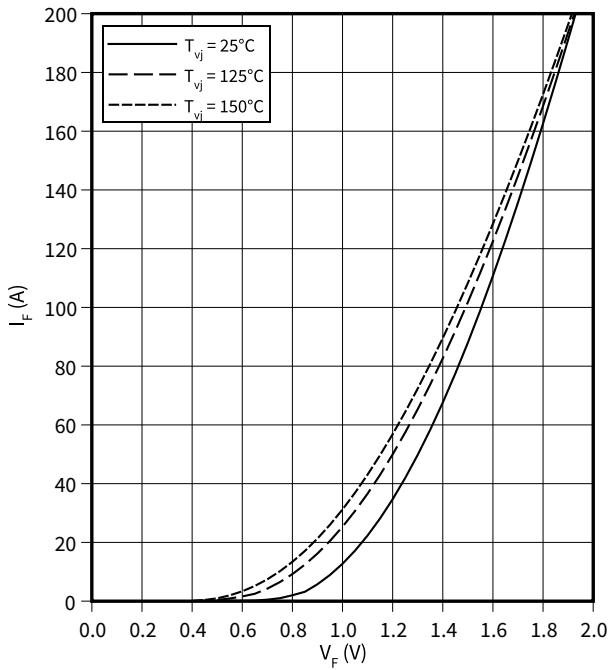
$I_C = f(V_{CE})$

$R_{Goff} = 1.5 \Omega$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 150^\circ\text{C}$



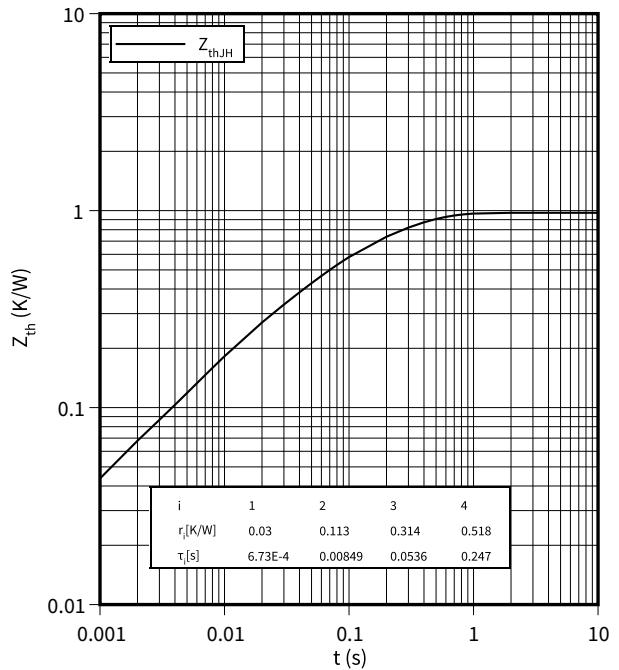
Forward characteristic (typical), Diode, D1 / D4

$I_F = f(V_F)$



Transient thermal impedance, Diode, D1 / D4

$Z_{th} = f(t)$

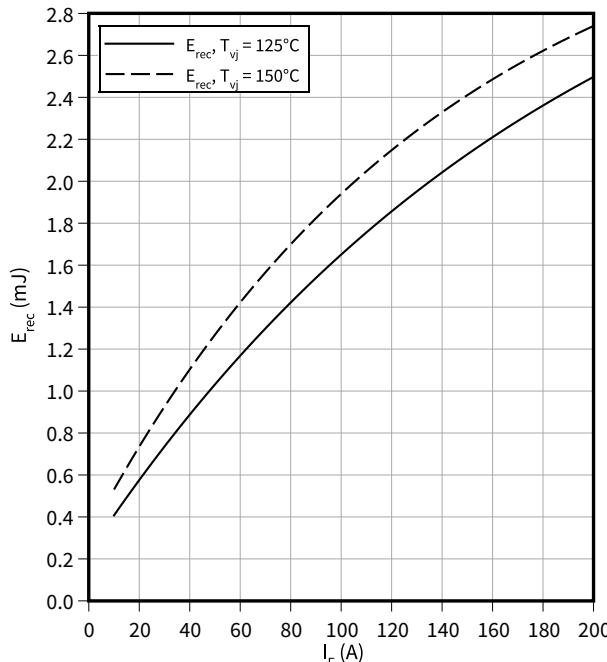


8 Characteristics diagrams

Switching losses (typical), Diode, D1 / D4

$$E_{rec} = f(I_F)$$

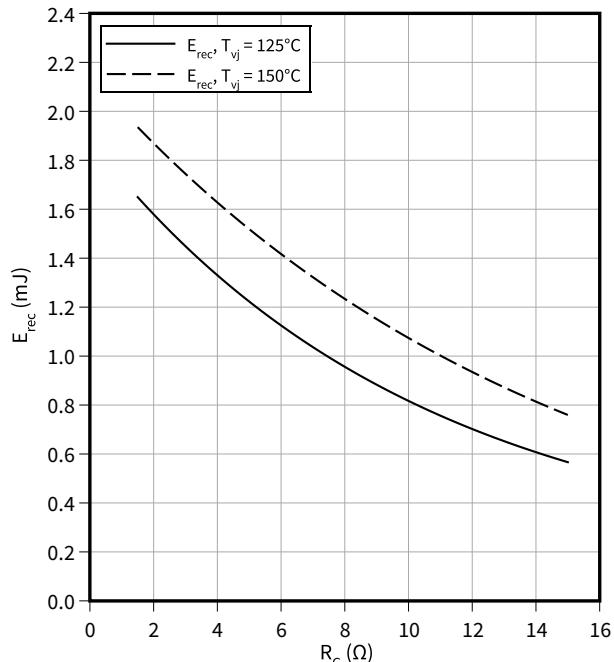
$$R_{Gon} = 1.5 \Omega, V_R = 300 \text{ V}$$



Switching losses (typical), Diode, D1 / D4

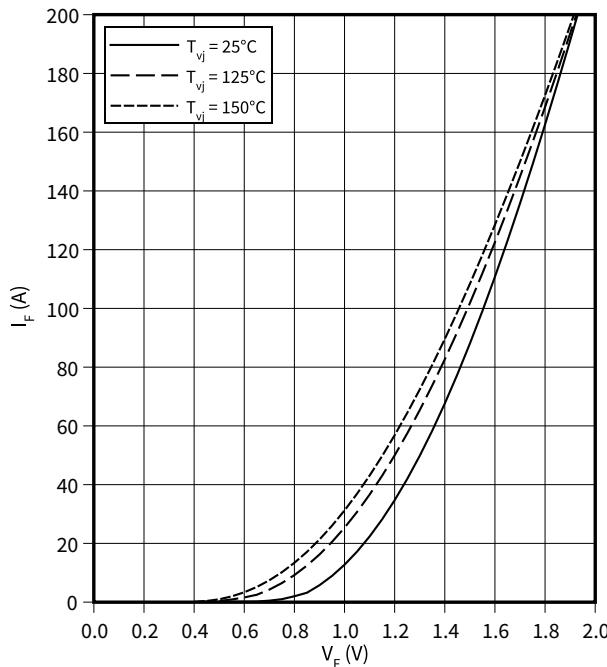
$$E_{rec} = f(R_G)$$

$$I_F = 100 \text{ A}, V_R = 300 \text{ V}$$



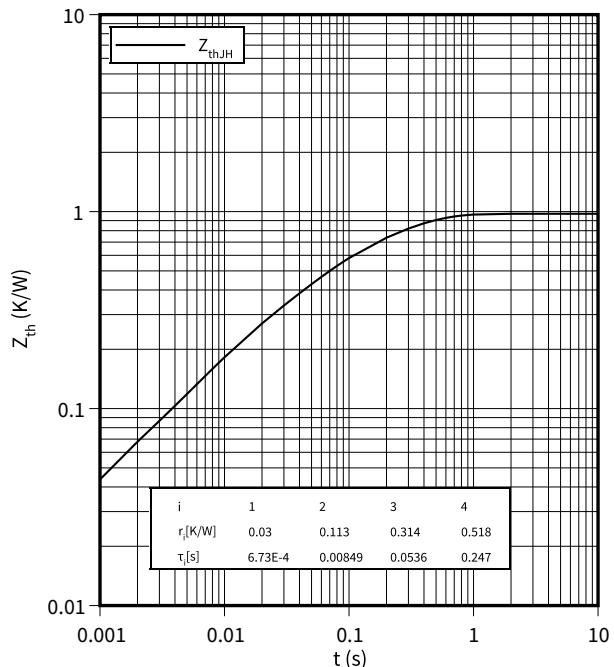
Forward characteristic (typical), Diode, D2 / D3

$$I_F = f(V_F)$$



Transient thermal impedance, Diode, D2 / D3

$$Z_{th} = f(t)$$

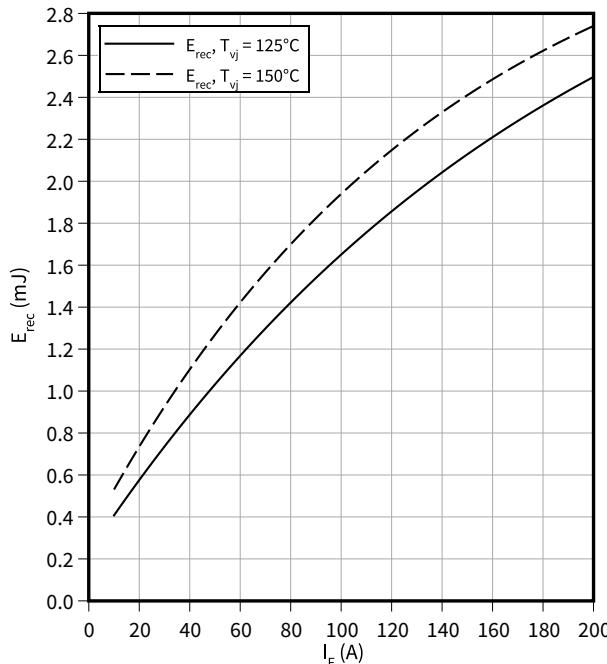


8 Characteristics diagrams

Switching losses (typical), Diode, D2 / D3

$$E_{rec} = f(I_F)$$

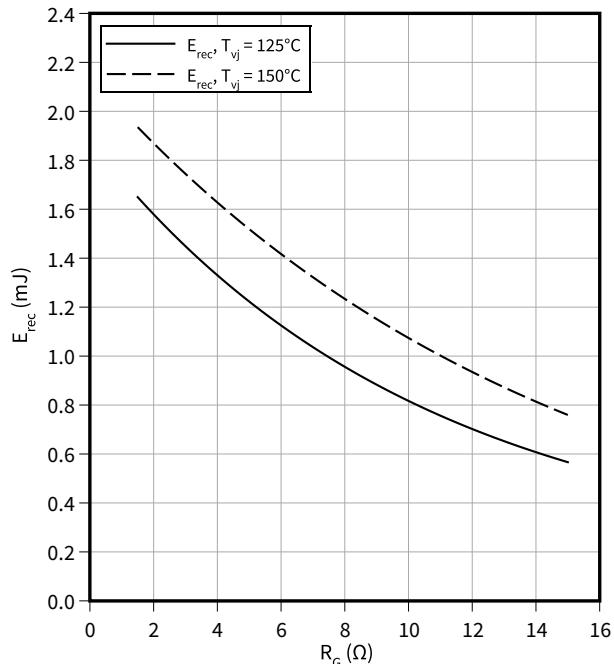
$$R_{Gon} = 1.5 \Omega, V_R = 300 \text{ V}$$



Switching losses (typical), Diode, D2 / D3

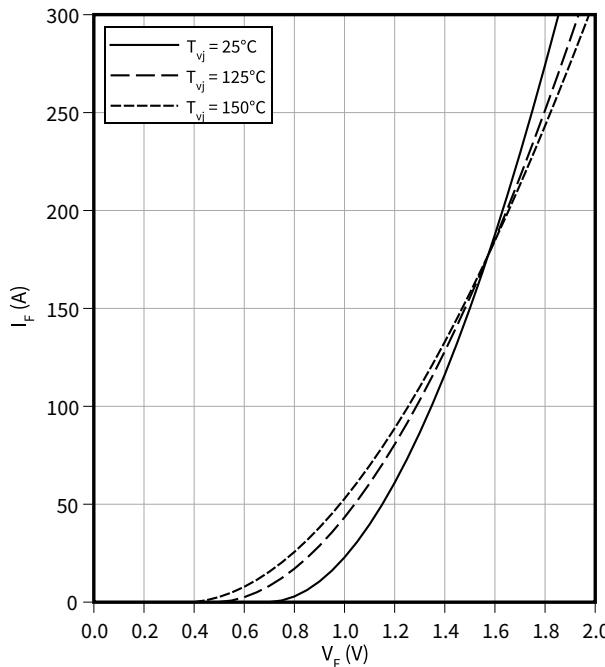
$$E_{rec} = f(R_G)$$

$$I_F = 100 \text{ A}, V_R = 300 \text{ V}$$



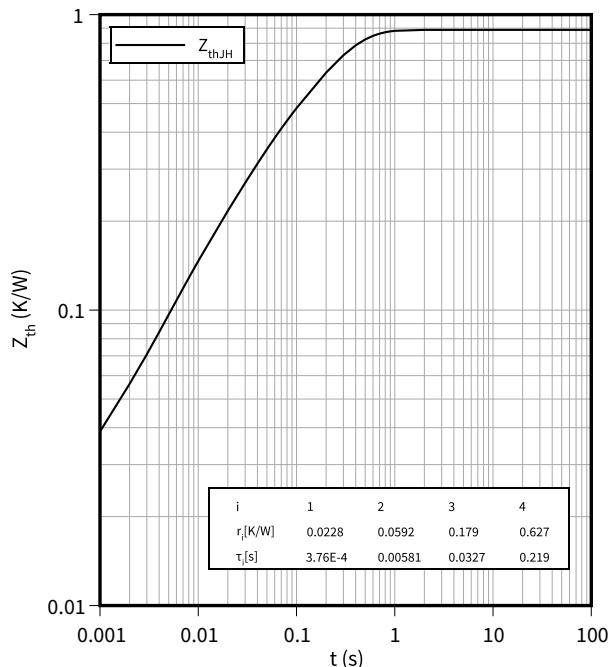
Forward characteristic (typical), Diode, D5 / D6

$$I_F = f(V_F)$$



Transient thermal impedance, Diode, D5 / D6

$$Z_{th} = f(t)$$

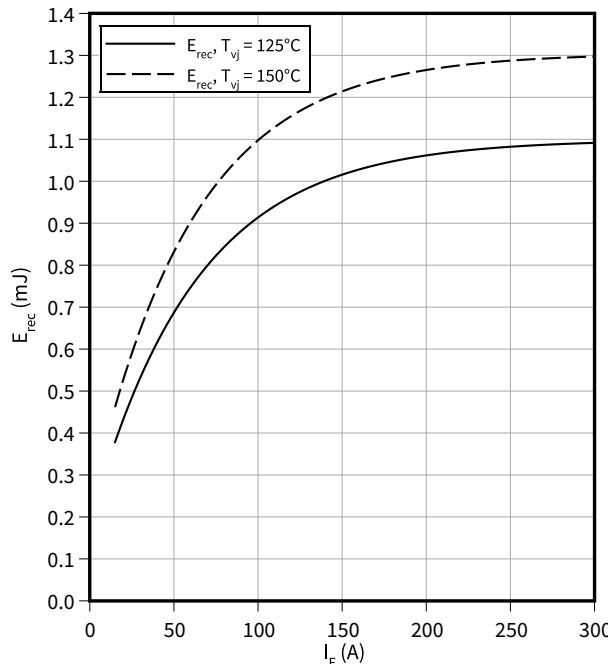


8 Characteristics diagrams

Switching losses (typical), Diode, D5 / D6

$$E_{rec} = f(I_F)$$

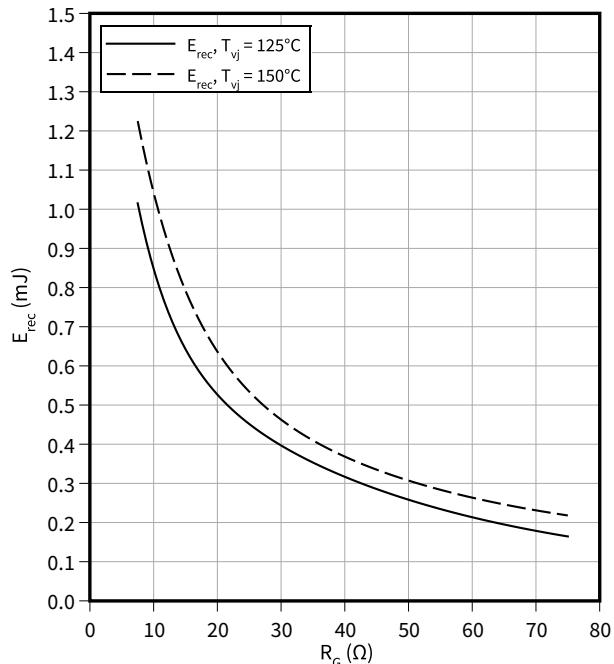
$$R_{Gon} = 7.5 \Omega, V_R = 300 \text{ V}$$



Switching losses (typical), Diode, D5 / D6

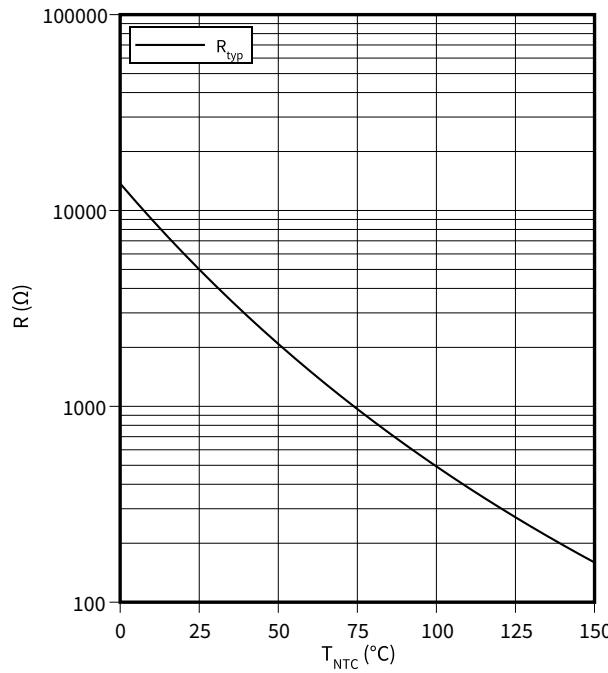
$$E_{rec} = f(R_G)$$

$$I_F = 150 \text{ A}, V_R = 300 \text{ V}$$



Temperature characteristic (typical), NTC-Thermistor

$$R = f(T_{NTC})$$



9 Circuit diagram

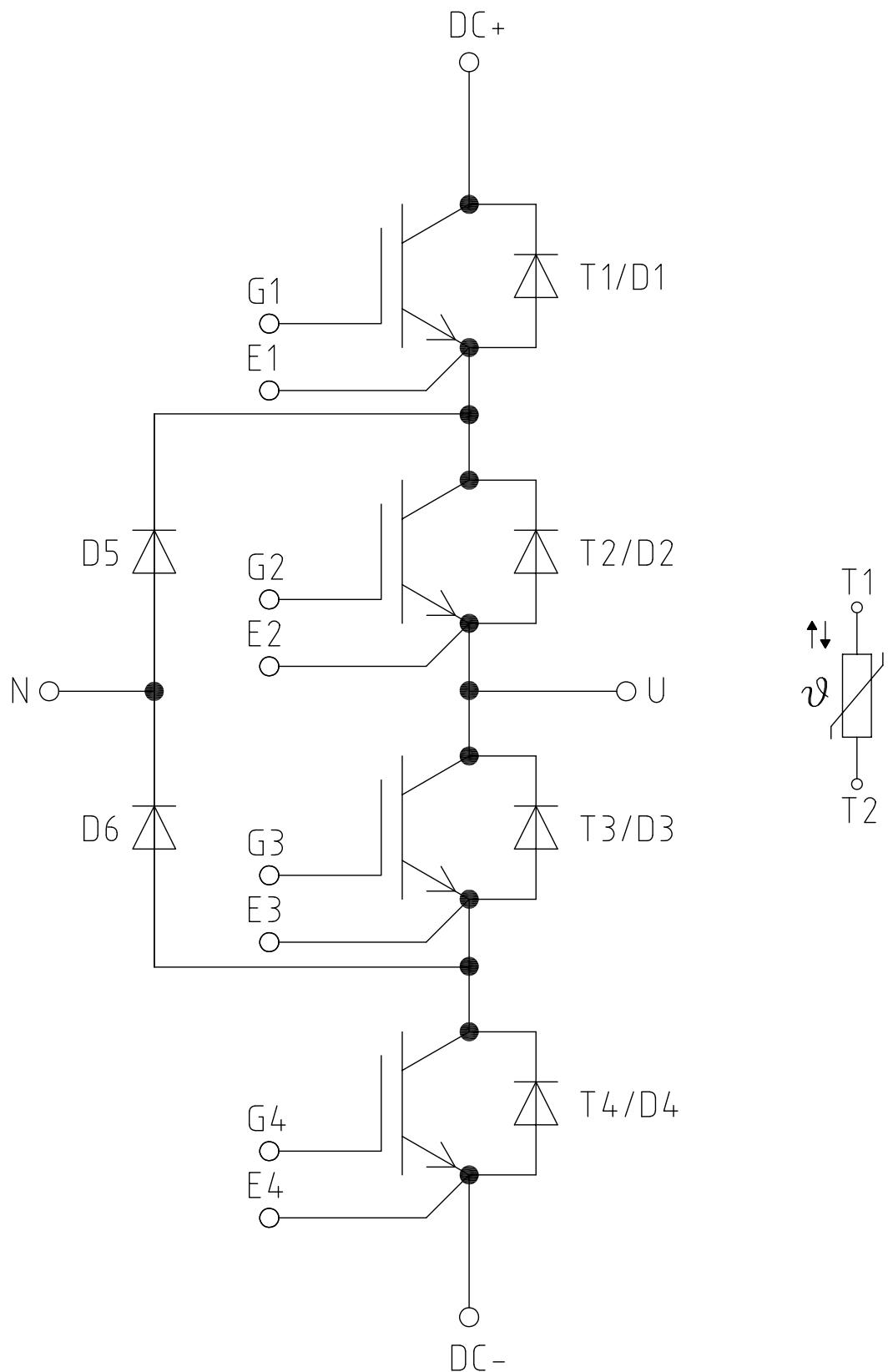


Figure 1

10 Package outlines

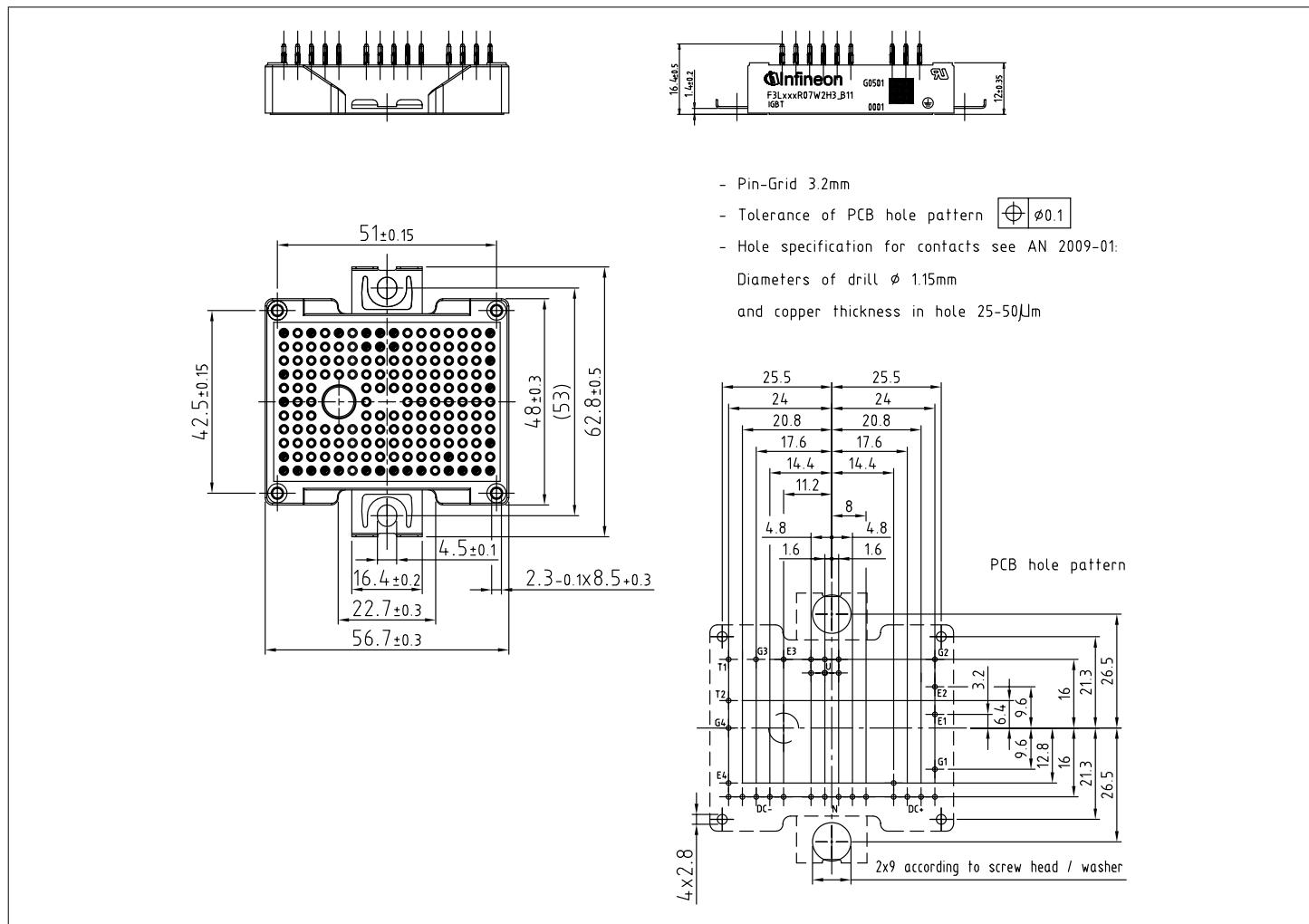


Figure 2

11 Module label code

11 Module label code

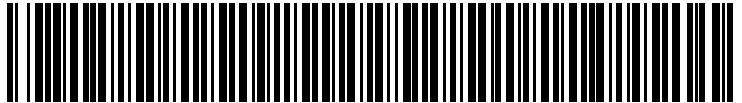
Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	<i>Content</i> Module serial number Module material number Production order number Date code (production year) Date code (production week)	<i>Digit</i> 1 – 5 6 - 11 12 - 19 20 – 21 22 – 23	<i>Example</i> 71549 142846 55054991 15 30
Example	 71549142846550549911530	 71549142846550549911530	

Figure 3

Revision history

Revision history

Document revision	Date of release	Description of changes
0.10	2021-08-24	Initial version
1.00	2021-12-13	Final datasheet

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**Document reference
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